

R-C Thermal Model Parameters

DESCRIPTION

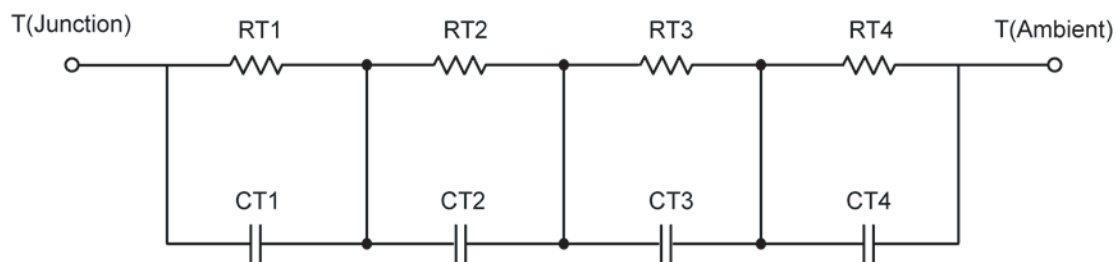
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

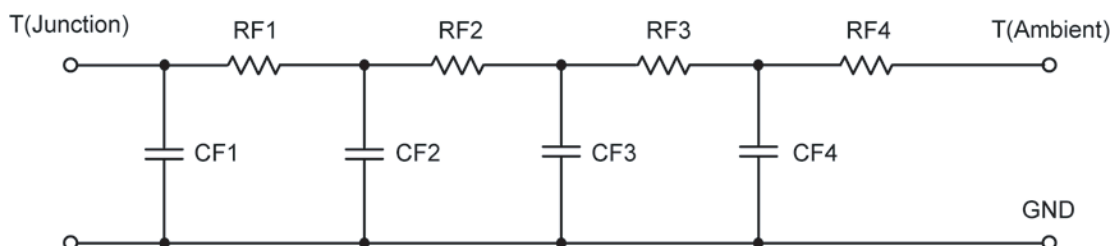
For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	12.0595	N/A	3.6605
RT2	35.2638	N/A	28.2515
RT3	24.3406	N/A	11.4120
RT4	48.3361	N/A	8.6760
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	938.7042 u	N/A	385.8641 u
CT2	32.0396 m	N/A	18.6751 m
CT3	27.4358 m	N/A	162.0668 m
CT4	1.4376	N/A	4.3131 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	13.4880	N/A	6.4577
RF2	33.0793	N/A	14.1264
RF3	27.8159	N/A	16.9454
RF4	45.6168	N/A	14.4705
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	1.0062 m	N/A	451.9417 u
CF2	11.4267 m	N/A	5.1870 m
CF3	19.1510 m	N/A	13.0853 m
CF4	1.6009	N/A	36.9671 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

